

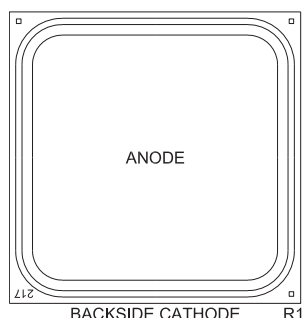
The CPD32X Schottky die is optimized for alternative energy applications. The 6 mil thick die provides an ultra low profile that is readily attached via standard die attach methods. Parametrically, the device is extremely energy efficient as a result of low forward and reverse conduction losses.

FEATURES:

- Low forward voltage at 10 Amps forward current
- Low reverse leakage current
- Low profile geometry
- Metalization suitable for standard die attach technologies
- Top metalization optimized for wire bonding

APPLICATIONS:

The CPD32X is optimized for use as a by-pass rectifier in low profile solar (PV) panels.



MECHANICAL SPECIFICATIONS:

Die Size	85 x 85 MILS
Die Thickness	5.9 MILS ± 0.8 MILS
Die Passivation	SiN
Anode Bonding Pad Area	75 x 75 MILS
Top Side Metalization	Al – 30,000Å
Back Side Metalization	Ti/Ni/Au – 1,600Å/5,550Å/1,500Å
Scribe Alley Width	3.15 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	2,260

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	40	V
DC Blocking Voltage	V _R	40	V
Average Forward Current	I _O	10	A
Peak Forward Surge Current (tp=8.3ms)	I _{FSM}	250	A
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =10V		10	200	μA
I _R	V _R =40V		30	500	μA
I _R	V _R =40V, T _A =100°C		15	50	mA
BV _R	I _R =0.5mA	40			V
V _F	I _F =5.0A		0.43	0.48	V
V _F	I _F =10A		0.48	0.52	V

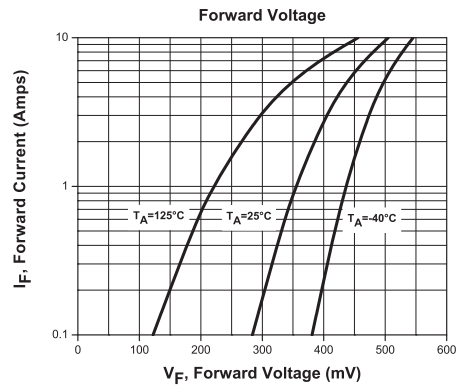
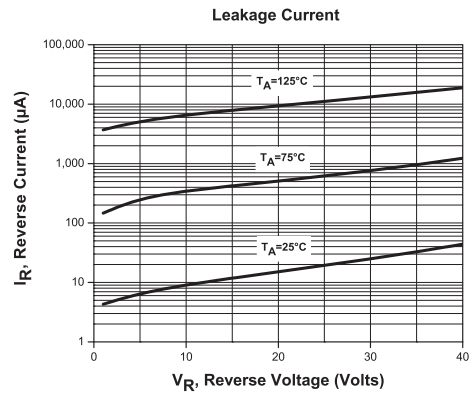
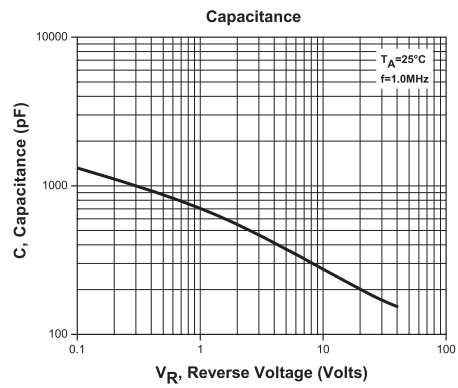
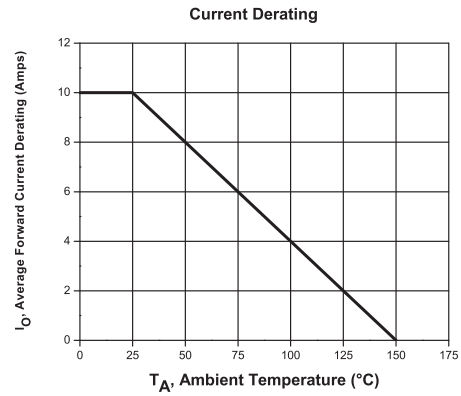
PACKING OPTIONS:

- CPD32X-WN: Full Wafer
- CPD32X-WR: Sawn Wafer on Plastic Ring

R3 (2-December 2011)

CPD32X

Typical Electrical Characteristics



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